Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	3977	Ion adj traps	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/08/18 13:24
L2	14	1 and (fabric$5 near4 dielectric)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/08/18 13:30
L3	40	1 and (fabric$5 near4 semiconductor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/08/18 13:47
L4	8	3 and (etch$3 near4 electrode)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/08/18 13:31
L5	20	3 and (form$3 near4 electrode)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/08/18 13:32
L6	8	1 and (alternate near4 layers)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/08/18 14:23
L7	2091922	1 and fabrication or manufacturing	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/08/18 13:58
L8	505	1 and (fabrication or manufacturing)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/08/18 13:59

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L9	505	8 and (ion near4 traps)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/08/18 13:59
L10	244	1 and (fabrication or manufacturing near4 ion adj traps)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/08/18 14:00
L11	0	10 and (alternate near4 conducting adj layers)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/08/18 14:01
L12	2	10 and (etch$3 near4 cavity)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/08/18 14:06
L13	4	"6,469,298"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/08/18 14:10
L14	14	"6,459,080"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/08/18 14:11
L15	15	"5,793,091"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/08/18 14:12
L16	8	1 and (alternate near6 layers)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/08/18 14:31

L17	241	Ion adj traps and fabrication	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/08/18 14:32
L18	6	17 and (alternate near4 layers)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/08/18 15:07
L19	3482	((250/299,292,282,288,) or (216/2,) or (313/256,)).CCLS.	USPAT	OR	OFF	2005/08/18 15:07
L20	19	19 and (alternate near4 layers)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/08/18 15:09
L21	1770	19 and (etch$3 near4 cavity or electrode)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/08/18 15:08
L22	15	21 and (alternate near4 layers)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/08/18 15:09